

WHAT IS CLAIMED IS:

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1. A contact structure for electrically connecting a connecting wiring over a substrate to a wiring over another substrate by means of an anisotropic conductive film, wherein said connecting wiring is a lamination film formed of a metallic film and a transparent conductive film, and

in a connecting portion with said anisotropic conductive film, a side surface of said metallic film is covered with a protecting film.

2. The contact structure of claim 1 wherein the protecting film is a resin film.

3. The contact structure of claim 1 wherein a thickness of the metallic film is between 100 nm and 1 μm .

4. The contact structure of claim 1 wherein the metallic film comprises a metallic layer having Al as its principal constituent, or an alloy layer containing Al.

5. The contact structure of claim 1 wherein the metallic film comprises a metallic layer having W as its principal constituent, or an alloy layer containing W.

6. The contact structure of claim 1 wherein the metallic film is a lamination film formed of a W layer and an alloy layer containing W and N.

7. The contact structure of claim 1 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μm .

8. The contact structure of claim 1 wherein the transparent conductive film is an alloy film containing zinc oxide.

9. The contact structure of claim 1 wherein the transparent conductive film is an alloy film containing zinc oxide and indium oxide.

10. A contact structure for electrically connecting a connecting wiring over a substrate to a wiring over another substrate by means of an anisotropic conductive film, wherein said connecting wiring is a lamination film formed of a metallic film and a transparent conductive film, and only said transparent conductive film is in contact with said anisotropic conductive film.

11. The contact structure of claim 10 wherein the protecting film is a resin film.

12. The contact structure of claim 10 wherein a thickness of the metallic film is between 100 nm and 1 μ m.

13. The contact structure of claim 10 wherein the metallic film comprises a metallic layer having Al as its principal constituent, or an alloy layer containing Al.

14. The contact structure of claim 10 wherein the metallic film comprises a metallic layer having W as its principal constituent, or an alloy layer containing W.

15. The contact structure of claim 10 wherein the metallic film is a lamination film formed of a W layer and an alloy layer containing W and N .

16. The contact structure of claim 10 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μm .

17. The contact structure of claim 10 wherein the transparent conductive film is an alloy film containing zinc oxide.

18. The contact structure of claim 10 wherein the transparent conductive film is an alloy film containing zinc oxide and indium oxide.

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19. A semiconductor device comprising:
a circuit structured with a thin film transistor over a substrate; and
a connecting wiring over said substrate for connecting the circuit structured with the thin film transistor to another circuit,
wherein said connecting wiring is a lamination film of a metallic film and a transparent conductive film, and
a side surface of said metallic film is covered with a protecting film at a connecting portion with the other circuit.

20. A semiconductor device of claims 19 wherein the protecting film is formed of the same materials as that of an insulating film between a gate wiring and a source wiring of the thin film transistor.

Sub 38
21. A semiconductor device of claims 19 wherein the connecting wiring is electrically connected to a wiring of the other substrate via the anisotropic conductive film.

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22. A semiconductor device of claims 19 wherein the protecting film is a resin film.

23. A semiconductor device of claims 19 wherein a thickness of the metallic film is between 100 nm and 1 μ m.

24. A semiconductor device of claims 19 wherein the metallic film comprises a metallic layer having Al as its principal constituent, or an alloy layer containing Al.

25. A semiconductor device of claims 19 wherein the metallic film comprises a metallic layer having W as its principal constituent, or an alloy layer containing W.

26. A semiconductor device of claims 19 wherein the metallic film is a lamination film formed of a W layer, and an alloy layer containing W and N.

27. A semiconductor device of claims 19 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μ m.

28. A semiconductor device of claims 19 wherein the transparent conductive film is an alloy film containing zinc oxide.

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29. A semiconductor device of claims 19 wherein the transparent conductive film is an alloy film containing zinc oxide and indium oxide.

30. The device of claim 19 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

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31. A semiconductor device comprising:
a first substrate having a circuit structured with a thin film transistor;
a second substrate opposing said first substrate;
a connecting wiring formed of a metallic film and a transparent conductive film in contact with the metallic film surface for connecting said circuit structured with a thin film transistor to another circuit; and
a protecting film in contact with a side surface of said metallic film,
wherein said connecting wiring and said protecting film are formed over said first substrate.

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32. A semiconductor device of claims 31 wherein the protecting film is formed of the same materials as that of an insulating film between a gate wiring and a source wiring of the thin film transistor.

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33. A semiconductor device of claims 31 wherein the connecting wiring is electrically connected to a wiring of the other substrate via the anisotropic conductive film.

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34. A semiconductor device of claims 31 wherein the protecting film is a resin film.

35. A semiconductor device of claims 31 wherein a thickness of the metallic film is between 100 nm and 1 μm .

36. A semiconductor device of claims 31 wherein the metallic film comprises a metallic layer having Al as its principal constituent, or an alloy layer containing Al.

37. A semiconductor device of claims 31 wherein the metallic film comprises a metallic layer having W as its principal constituent, or an alloy layer containing W.

38. A semiconductor device of claims 31 wherein the metallic film is a lamination film formed of a W layer, and an alloy layer containing W and N.

39. A semiconductor device of claims 31 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μm .

40. A semiconductor device of claims 31 wherein the transparent conductive film is an alloy film containing zinc oxide.

41. A semiconductor device of claims 31 wherein the transparent conductive film is an alloy film containing zinc oxide and indium oxide.

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42. The device of claim 31 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

43. A semiconductor device comprising:

a first substrate having a circuit structured with a thin film transistor;

a second substrate opposing said first substrate;

a connecting wiring formed of a metallic film and a transparent conductive film in contact with the metallic film surface for connecting said circuit structured with a thin film transistor to another circuit;

a column-shape spacer formed over said thin film transistor for maintaining a space between said first substrate and said second substrate; and

a protecting film in contact with a side surface of said metallic film formed of a same material as that of the column-shape spacer,

wherein said connecting wiring, said column spacer, and said protecting film are formed over said first substrate.

44. A semiconductor device of claims 43 wherein the connecting wiring is electrically connected to a wiring of the other substrate via the anisotropic conductive film.

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45. A semiconductor device of claims 43 wherein the protecting film is a resin film.

46. A semiconductor device of claims 43 wherein a thickness of the metallic film is between 100 nm and 1 μ m.

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47. A semiconductor device of claims 43 wherein the metallic film comprises a metallic layer having Al as its principal constituent, or an alloy layer containing Al.

48. A semiconductor device of claims 43 wherein the metallic film comprises a metallic layer having W as its principal constituent, or an alloy layer containing W.

49. A semiconductor device of claims 43 wherein the metallic film is a lamination film formed of a W layer, and an alloy layer containing W and N.

50. A semiconductor device of claims 43 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μm .

51. A semiconductor device of claims 43 wherein the transparent conductive film is an alloy film containing zinc oxide.

52. A semiconductor device of claims 43 wherein the transparent conductive film is an alloy film containing zinc oxide and indium oxide.

53. The device of claim 43 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

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